

Product Change Notification - JAON-06DZOX216

Date: 08 Oct 2015

Product Category: Supertex

Notification subject: CCB 1409.34 Final Notice - Additional Fabrication Site: Qualification of an additional fabrication site for LND150 and LND250 Supertex device families.

Notification text:

PCN Status:

Final notification

Microchip Parts Affected:

Please open the attachments found in the attachments field below labeled as PCN_#_Affected_CPN.

NOTE: For your convenience Microchip includes identical files in two formats (.pdf and .xls).

Description of Change:

Qualification of an additional fabrication site for LND150 and LND250 Supertex device families.

Pre Change:

Fabricated at SPTX fab site.

Post Change:

Fabricated at Microchip FAB2 fab site.

Impacts to Data Sheet:

No

Reason for Change:

To improve productivity as part of the integration of Supertex and Microchip.

NOTE: SPTX does not have the ability to start additional wafers since Q4 of CY14.

Change Implementation Status:

Complete

Estimated First Ship Date:

October 16, 2015 (date code: 1542)

NOTE: Please be advised that after the estimated first ship date customers may receive pre and post change parts.

Markings to Distinguish Revised from Unrevised Devices:

Traceability code

Revision History:

July 15, 2014: Issued initial notification as PCN number JAON-15TRYZ317.

August 14, 2014: Revised the initial notification by revising the CPN list to include all parts that are moving to FAB2, adding the note after the reason for change, and revising the customer letter to show that Supertex customers may register for Microchip's PCN email service.

October 08, 2015: Issued final notification. Attached the Qualification Report. Updated Impacts to Data Sheet from TBD to No. Revised the estimated first ship date from September 12, 2014 to October 16, 2015.

The change described in this P_{CN} does not alter Microchip's current regulatory compliance regarding the material content of the applicable products.

Attachment(s): [PCN JAON-06DZOX216 Qual Report.pdf](#) [PCN JAON-06DZOX216 Affected CPN.pdf](#) [PCN JAON-06DZOX216 Affected CPN.xls](#)

Please contact your local [Microchip sales office](#) with questions or concerns regarding this notification.

Terms and Conditions:

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Affected Catalog Part Numbers (CPN)

PCN_JAON-06DZOX216
CATALOG_PART_NBR
LND150K1-G
LND150N3-G
LND150N3-G-P002
LND150N3-G-P003
LND150N3-G-P013
LND150N3-G-P014
LND150N8-G
LND150ND-APX
LND250K1-G



PCN #: JAON-06DZOX216

Date
September 28, 2015

**Qualification of an additional fabrication site for LND150 and
LND250 Supertex device families.**

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QUALIFICATION DATA

High Temperature Operating Life: High Temperature Reverse Bias (HTRB)

Test Method	Mil-STD 750, M1042, Condition A
Test Condition	150°C / 1000 hours
Sample Size (45 ea. min)	(Fail/Pass)
Lot 1	0/45 ^a

^a Pre & Post testing was conducted at room temperature, ~25°C.

High Temperature Operating Life: High Temperature Gate Bias (HTGB)

Test Method	Mil-STD 750, M1042, Condition B
Test Condition	150°C / 1000 hours
Sample Size (45 ea. min)	(Fail/Pass)
Lot 1	0/45 ^a

^a Pre & Post testing was conducted at room temperature, ~25°C.

ESD

Test	Pin Combination	Sample Size	Pass Voltage
ESD-HBM	Gate to Drain/Source ^a	Lot 1 = 9 ^a	±0.9kV ^b
ESD-HBM	Drain to Gain/Source ^a	Lot 1 = 9 ^a	±2.7kV ^b
ESD-HBM	Source to Drain/Gate	Lot 1 = 12 ^a	±2.4kV ^b
ESD-HBM	Gate to Source ^a	Lot 1 = 6 ^a	±0.8kV ^b
ESD-HBM	Gate to Drain ^a	Lot 1 = 6 ^a	±0.9kV ^b

^a Class 1B as per the Mil-Std 750 M1020

^b Pre & Post testing was conducted at room temperature, ~25°C